RUTTONSHA

Ruttonsha International Rectifier Ltd.

SILICON CONTROLLED RECTIFIERS

High Power Thyristor
Hockey Puk Version
E-PUK Series 500PE

Types 500 PE 200 to 300

FEATURES

- *Center amplifying gate.*
- *International standard case TO-200AB (E-PUK)*
- *High profile hockey - puk.*

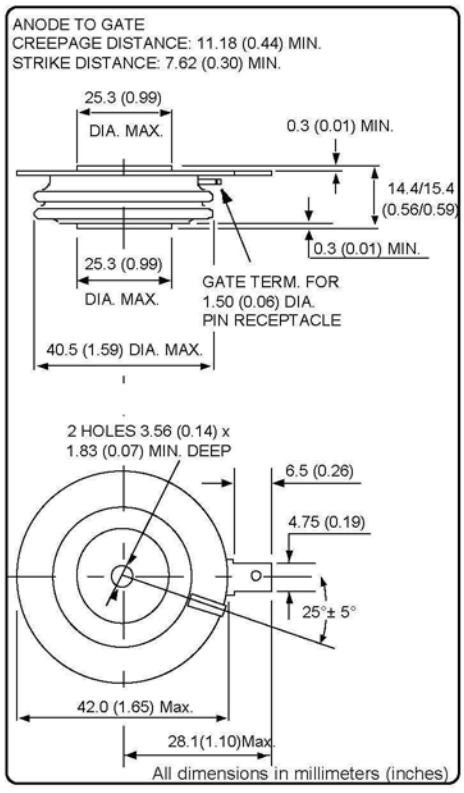
TYPICAL APPLICATIONS

- *DC motor control (e.g. for machine tools).*
- *Controlled rectifiers (e.g. for battery charging, UPS).*
- *AC controllers (e.g. for temperature control, lights control).*

500 PE ...

MAJOR RATINGS & CHARACTERISTICS

Parameters		500PE	Units
$I_{T(AV)}$		510	A
	@ T_{hs}	55	^{0}C
$I_{T(RMS)}$		800	A
	@ T_{hs}	25	^{0}C
I_{TSM}	@ 50 Hz	4500	A
I^2t	@ 50 Hz	101	KA^{2}s
V_{DRM} / V_{RRM}		2000 to 3000	V
T_J		-40 to 125	^{0}C



SILICON CONTROLLED RECTIFIERS

SERIES: 500PE 300

ELECTRICAL SPECIFICATION

VOLTAGE RATINGS

Type Number	Voltage Code	V_{RRM} / V_{DRM}, max. repetitive peak and off-state voltage V	V_{RSM}, max. non-repetitive peak voltage V	I_{DRM} / I_{RRM} max. @ 125°C mA
500PE	200	2000	2100	60
	220	2200	2300	
	240	2400	2500	
	260	2600	2700	
	280	2800	2900	
	300	3000	3100	

ON-STATE CONDUCTION

	Parameter	500PE	Units	Conditions	
$I_{T(AV)}$	Max. average on-state current	510	A	180° conduction, half sine wave	
	@ heat sink temperature	55	°C	double side cooled	
$I_{T(RMS)}$	Max. RMS on-state current	800	A	@25°C heat sink temperature (double side cooled)	
I_{TSM}	Max. peak one cycle non-repetitive surge current	4500		t = 10ms	Sinusodial half Wave Initial $T_J = T_J$ max.
I^2t	Maximum I^2t for fusing	101	kA^2s	t = 10ms	
$V_{T(TO)}$	Threshold voltage	1.10	V	$T_J = T_J$ max.	
r_t	On state slope resistance	1.60	mΩ	$T_J = T_J$ max.	
V_{TM}	Max. on state voltage	2.80	V	I_{pk} =1000A, T_J = 125°C, t_p = 10ms sine pulse	
I_H	Maximum holding current	600	mA	T_J = 25°C, anode supply 12V resistive load	
I_L	Latching current	1000			

SWITCHING

	Parameter	500PE	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	100	A/µs	Gate drive 20V, 20Ω, tr ≤ 1 µs T_J = 125°C, anode voltage ≤ 80% V_{DRM}
t_d	Typical delay time	1.0	µs	Gate current 1A, di_g/dt = 1A/µs V_d = 0.67% V_{DRM}, T_J = 25°C

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BLOCKING

	Parameter	500PE	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/µs	T_J = 125°C, linear to 80% rated V_{DRM}
I_{RRM} I_{DRM}	Max. peak reverse and off-state leakage current	60	mA	T_J = 125°C, rated V_{DRM} /V_{RRM} applied

TRIGGERING

	Parameter	500PE		Units	Conditions	
P_{GM}	Maximum peak gate power	10.0		W	T_J = 125°C, $t_p \leq$ 5ms	
$P_{G(AV)}$	Maximum average gate power	2.0			T_J = 125°C, f= 50Hz, d% = 50	
I_{GM}	Max. peak positive gate current	3.0		A	T_J = 125°C, $t_p \leq$ 5ms	
$+V_{GM}$	Max. peak positive gate voltage	20		V	T_J = 125°C, $t_p \leq$ 5ms	
$-V_{GM}$	Max. peak negative gate voltage	5.0				
I_{GT}	DC gate current required to trigger	TYP. 100	MAX. 200	mA	T_J = 25°C	Max. required gate trigger/current / voltage are the lowest value which will trigger all units 12V anode-to-cathode applied.
V_{GT}	DC gate voltage required to trigger	1.8	3.0	V	T_J = 25°C	
I_{GD}	DC gate current not to trigger	10		mA	T_J = 125°C	Max. gate current / voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied.
V_{GD}	DC gate voltage not to trigger	0.25		V		

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	500PE	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	°C	
T_{stg}	Max. storage temperature range	-40 to 150		
$R_{thJ\text{-}hs}$	Max. thermal resistance, junction to heat sink	0.056	K/W	DC operation double side cooled
F	Mounting force, ±10%	9800	N	
wt	Approximate weight	83	g	
	Case style	E - PUK		See outline